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HVU17

Variable Capacitance Diode for VCO



ADE-208-021C(Z)

Rev. 3 Jun. 1996

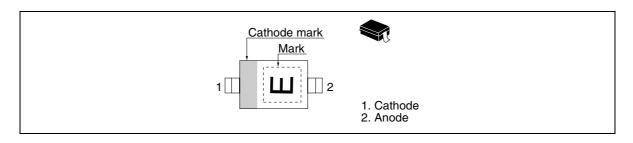
Features

- Good linearity of C-V curve.
- To be usable at low voltage.
- High figure of merit.
- Ultra small Resin Package (URP) is suitable for surface mount design.

Ordering Information

| Type No. | Laser Mark | Package Code |
|----------|------------|--------------|
| HVU17 | Е | URP |

Pin Arrangement



HVU17

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Value | Unit |
|----------------------|----------------|-------------|------|
| Reverse voltage | V _R | 15 | V |
| Junction temperature | Tj | 125 | °C |
| Storage temperature | Tstg | -55 to +125 | °C |

Electrical Characteristics

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Min | Тур | Max | Unit | Test Condition |
|-----------------------------|------------------|------|-----|------|------|---|
| Reverse voltage | V _R | 15.0 | _ | Å١ | V | $I_R = 10\mu A$ |
| Reverse current | I _R | _ | _ | 100 | nA | V _R = 9V |
| Capacitance | C ₁ | 50.0 | _ | 85.0 | pF | V _R = 1V, f = 1 MHz |
| | C ₃ | 16.1 | _ | 27.3 | _ | $V_R = 3V, f = 1 MHz$ |
| | C _{4.5} | 5.23 | _ | 8.84 | _ | V _R = 4.5V, f = 1 MHz |
| Capacitance ratio | n | 5.60 | _ | _ | _ | C ₁ / C _{4.5} |
| Figure of merit | Q | 50 | _ | _ | _ | V _R = 2.5V, f = 10 MHz |
| ESD-Capability ¹ | _ | 80 | _ | _ | V | C = 200pF , Both forward and reverse direction 1 pulse. |

Note: 1. Failure criterion; $I_R \ge 100$ nA at $V_R = 9$ V

Main Characteristic

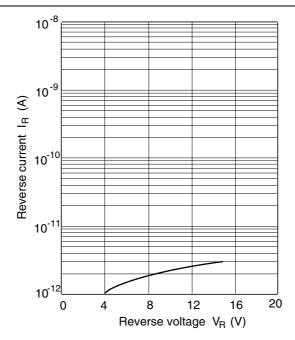


Fig.1 Reverse current Vs. Reverse voltage

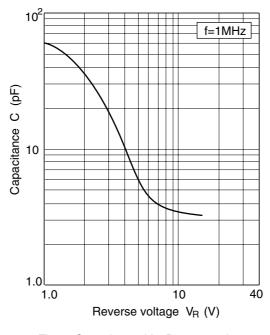
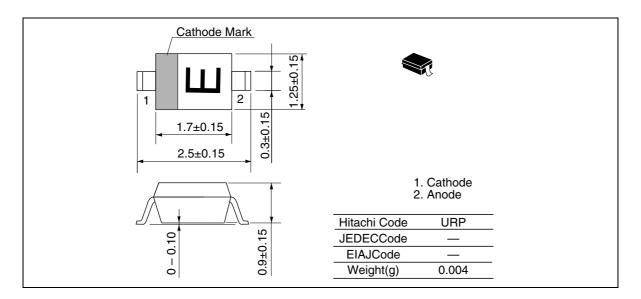


Fig.2 Capacitance Vs. Reverse voltage

Package Dimensions

Unit: mm



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